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(54) **METHODS FOR REDUCING LEAKAGE CURRENT**

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(57) **ABSTRACT**

Methods for forming a CPODE structure with reduced leakage current are disclosed herein. The CPODE structure is formed by etching away a pair of fins and forming a pair of trenches in the substrate where the pair of fins was originally located. A leakage path may be present in the area between the pair of fins. The etching is performed by cycling continuously plasma etch until the trenches are formed. The plasma etch removes any byproducts that may be formed during the fin etch which could reduce or stop the etching of the fins, the area between the pair of fins, and the substrate.

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